



Beam current measurement with logarithmic converter

C. Jamet, E. Petit

► To cite this version:

C. Jamet, E. Petit. Beam current measurement with logarithmic converter. Baron E. Lieuvain M. 15th International Conference on Cyclotrons and their Applications, Jun 1998, Caen, France. IOP Publishing, pp.293-296, 1999. <in2p3-00021788>

HAL Id: in2p3-00021788

<http://hal.in2p3.fr/in2p3-00021788>

Submitted on 29 Nov 2013

HAL is a multi-disciplinary open access archive for the deposit and dissemination of scientific research documents, whether they are published or not. The documents may come from teaching and research institutions in France or abroad, or from public or private research centers.

L'archive ouverte pluridisciplinaire **HAL**, est destinée au dépôt et à la diffusion de documents scientifiques de niveau recherche, publiés ou non, émanant des établissements d'enseignement et de recherche français ou étrangers, des laboratoires publics ou privés.

BEAM CURRENT MEASUREMENTS WITH LOGARITHMIC CONVERTER

C. Jamet, E.Petit
 Ganil, BP5027,14076 Caen Cedex

A new electronic device to measure low current has been developed for the new projects THI (High Intensity Transport) and SPIRAL at Ganil.

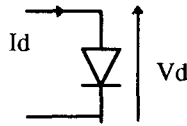
This electronic device gives a voltage proportionnal to the current logarithm. An analog to digital conversion of the voltage is realized. A calculation with the inverse logarithmic equation gives the current value.

The advantage of the logarithmic measurement is its possibility to measure a large scale without range changing. Developments and tests are now in progress to measure currents between picoamp to milliamp.

1 Principle of the logarithmic conversion

The logarithmic conversion uses the diode characteristic. The current-voltage characteristic of a diode is given by:

$$I_d = I_s(e^{\frac{V_d}{U_t}} - 1)$$



I_d : diode current
 I_s : reverse saturation current

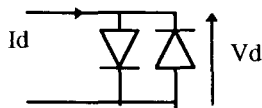
with $I_s = BT^3 e^{\frac{-E_g}{KT}}$
 E_g : band gap

V_d : diode voltage

$$U_t = \frac{kT}{q} \text{ with } k : \text{ Boltzmann's constant}$$

T : absolute temperature (K)
 q : electronic charge ($1,6 \cdot 10^{-19}$ C)

The used structure consists in connecting two diodes, with opposite polarities.



We find :

$$I_d = I_s \left(e^{\frac{V_d}{U_t}} - e^{-\frac{V_d}{U_t}} \right)$$

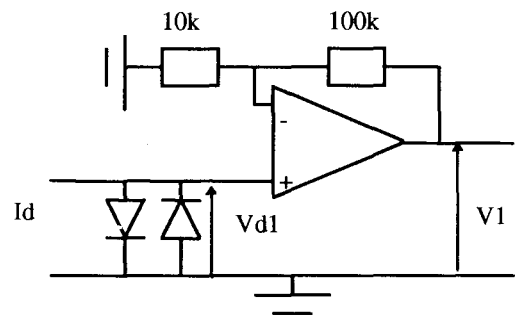
$$V_d = U_t \times \ln \left[\frac{1}{2} \left(\frac{I_d}{I_s} + \sqrt{\left(\frac{I_d}{I_s} \right)^2 + 4} \right) \right]$$

If $I_d/I_s \gg 2$

$$V_d \cong U_t \times \ln \left[\frac{I_d}{I_s} \right]$$

2 Two types of devices are used at GANIL.

2.1 Input stage with diodes upstream

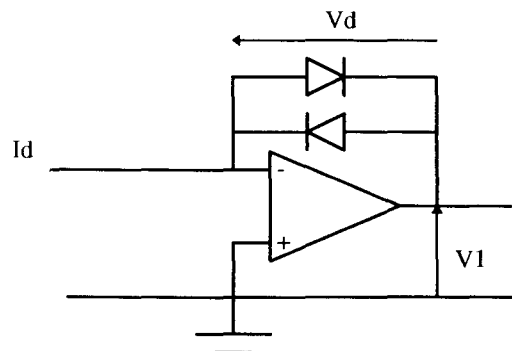


$$V1 = 11 * Vd1$$

The advantage of this kind of device is to heavily filter low currents. In parallel the capacitance of the cable and the input equivalent resistance of the electronic realize the filtering.

The disadvantage is that response time for low current becomes very long.

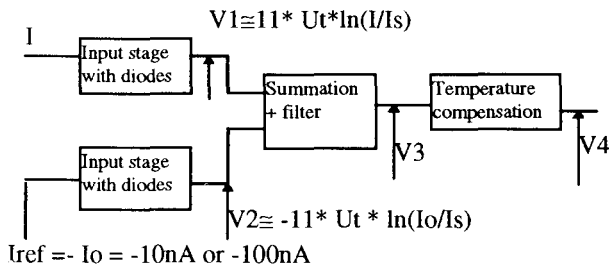
2.2 Input stage with diodes in feedback



$$V1 = -V_d$$

The response time is shorter than previous electronic, but it is more sensitive to electronic perturbations.

3 Layout of the electronic converter



4 Equation of converter

$$V3 = k \times (V1 + V2)$$

$$V3 \approx k \times 11 \times Ut \times \left(\ln\left(\frac{I}{I_s}\right) - \ln\left(\frac{I_o}{I_s}\right) \right) \approx K \times Ut \times \ln\left(\frac{I}{I_o}\right)$$

An electronic compensation corrects the effect of temperature on U_t and gives the gain 2v/decade.

$$V4 \approx 2 \times \log\left(\frac{I}{I_o}\right)$$

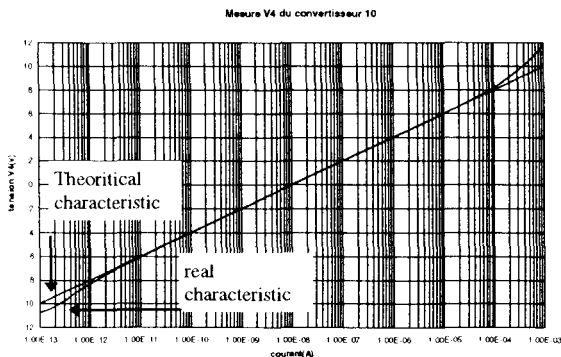
I_o : reference current (equal to 10nA or 100nA)

For the device with diodes in feedback we realize the same characteristic $V4=f(I)$.

$V4$ is include between -10v to 10v, so we can measure 10 decades of current.

5 Converter characteristic $V=f(I)$

For the logarithmic converter dedicated to SPIRAL, $I_o = 10nA$ and the theoretical characteristic is as shown on the figure.



In practice, I_{bias} (amplifier bias current) and I_s (reverse saturation current) make non-linearity in very low current ($< 10pA$). For the high current ($I > 100\mu A$) the resistance R_s of diode causes a non-linearity.

For the chosen diode (DPAD5 from TEMIC) we measure for $T=25^\circ C$:

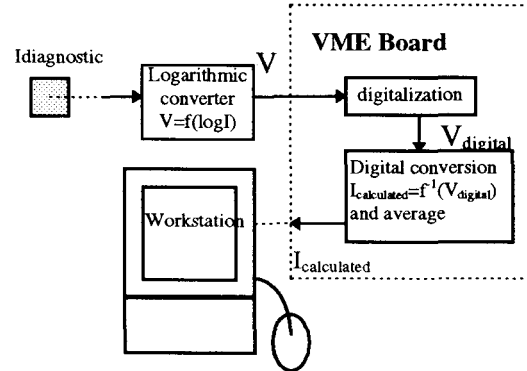
$I_s \approx 27fA$, $U_t \approx 27 mV$, $R_s \approx 55\Omega$

For the amplifier (OPA 129 from BURR-BROWN) we measure :

$I_{bias} \approx 117fA$

These values depend on the temperature.

6 Current calculation



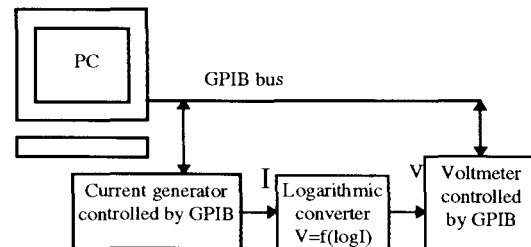
As seen before, the characteristic $V=f(I)$ isn't linear on the whole scale. We have a non-linearity for low current ($I < 10pA$) and high current ($I > 100\mu A$). The theoretical equation $V=2 * \log(I/I_o)$ and the inverse equation ($I_{calculated}=I_o * 10^{V/2}$) can't be used.

The selected solution consists in realizing a conversion table. Values of this table are located in an EPROM on the VME board.

7 Conversion table realization

To realize this table, we must acquire the characteristic $V=f(I)$ of each electronic converter. A test bench acquires values automatically.

Test bench description



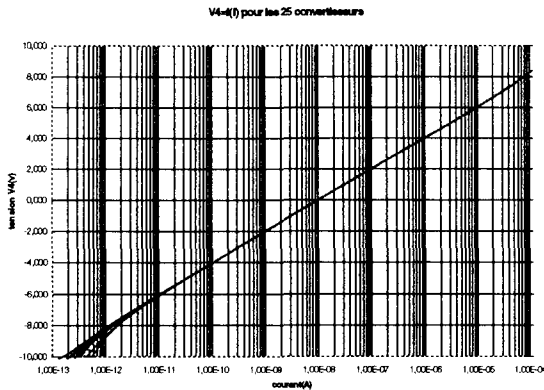
We acquire 1000 measurements of the characteristic $V=f(I)$. We choose an average characteristic and a computer program calculates the characteristic $I=f(V)$ with 4096 points. We use an analog to digital converter with 12 bits precision ($2^{12}=4096$ values).

We put the values in an EPROM on the VME board.

The microcontroller of the VME board acquires four voltages every 750µs. For all the values, the microcontroller calculates the corresponding currents, averages 400 current values and puts the result in the double access memory.

In practice, with the non-linearity the current can be measured between 0.3pA to 400µA.

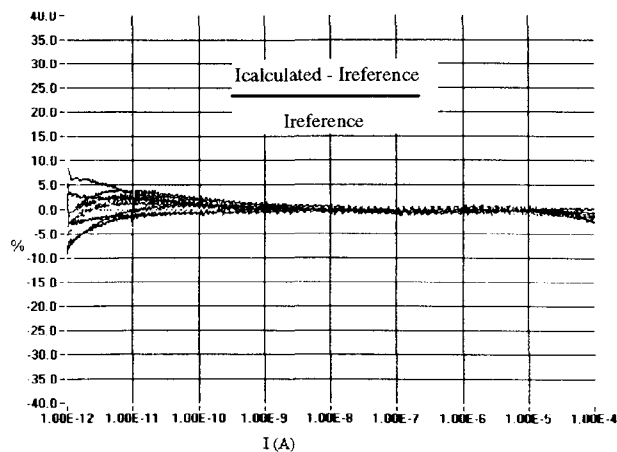
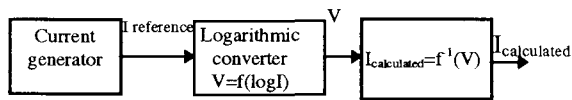
8 Characteristic V=f(I) of 25 converters



The different converters, for the same room temperature (25°C), have different characteristics for low current. These light differences are due to different values of Is.

9 Precision of the current calculation for 25 converters

A comparison of the reference current and the calculated current gives the precision of calculation with the microcontroller.



The precision for the low current ($i < 10^{-10}$ A) decreases because diodes have different characteristics.

10 Influence of the offset voltage

The equation of the converter is

$$V \cong 2 \times \log\left(\frac{I}{I_0}\right)$$

and the inverse equation is :

$$I_{calculated} \cong I_0 \times 10^{\frac{V}{2}}$$

If we have an offset voltage with V :

$$I_{calculated} \cong I_0 \times 10^{\frac{V+V_{offset}}{2}}$$

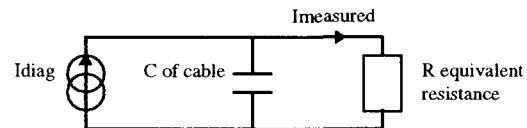
$$I_{calculated} \cong I_0 \times 10^{\frac{V}{2}} \times 10^{\frac{V_{offset}}{2}}$$

$$I_{calculated} \cong k \times I_0 \times 10^{\frac{V}{2}}$$

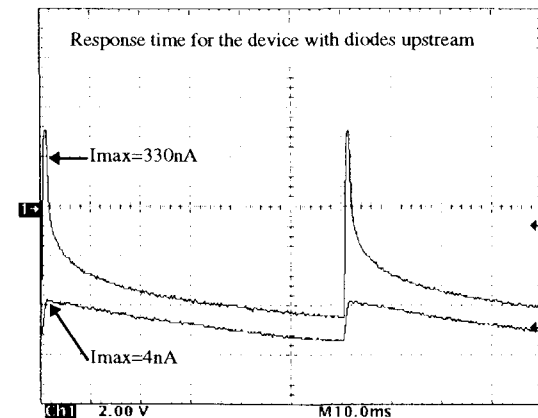
A difference of voltage gives, when we calculate the current, a multiplication factor. So it's very important to tune exactly the offset and the gain of the logarithmic converter.

11 Response time

The response time is due to the capacitance of the cable and the equivalent input resistance of the electronic. This resistance depends on the current value.

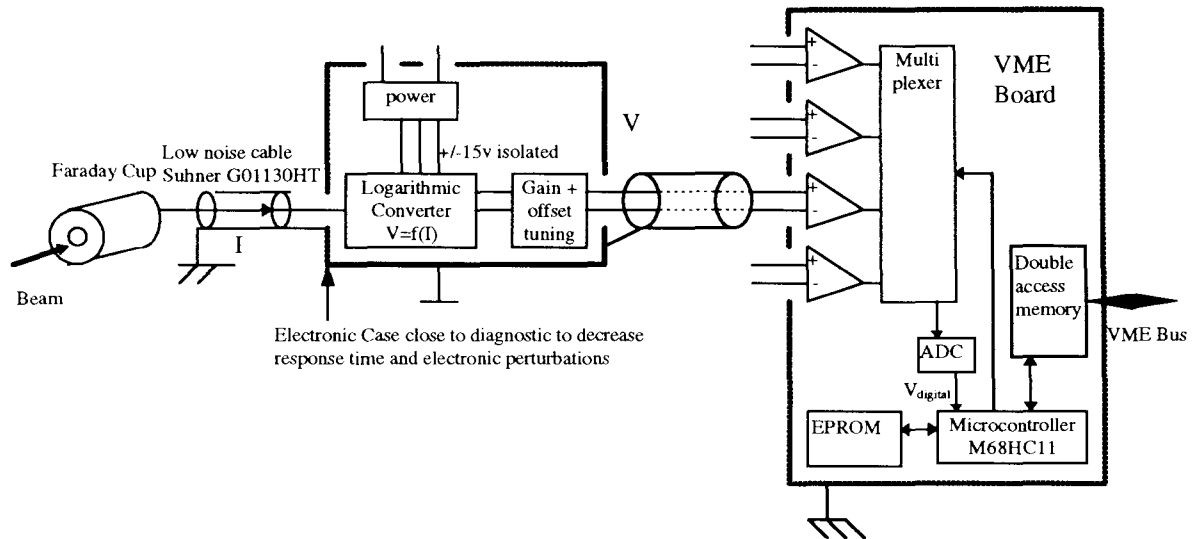


A chopper cuts the beam, a pulse of current during 0.8 ms is received on a faraday cup.



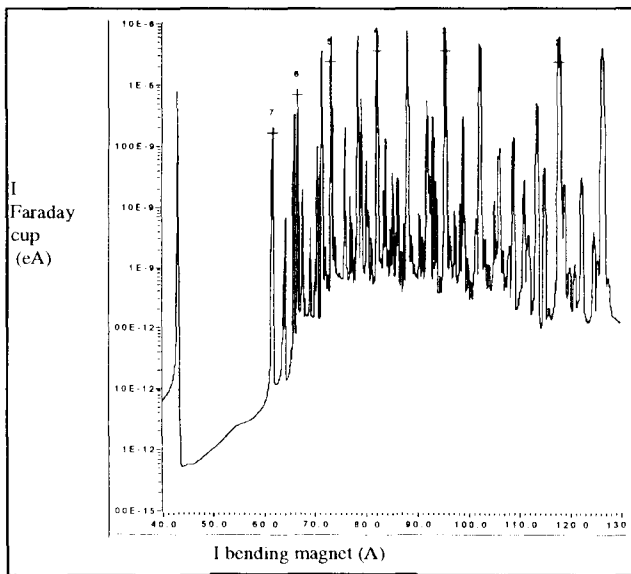
The response time increases when the current value decreases.

12 Layout of SPIRAL low current measurements



13 Charge state distribution of the experimental source

An exemple of measurements with logarithmic converter is given in the next figure.



We can see on the same curve different charge states which have maximum value completely different.

14 Conclusion

Logarithmic converters can measure current on a very large scale (10 decades) without range changing. The precision is about +/- 2% on the scale except for the current < 10pA. A filtering, with the cable capacitance and the equivalent input resistance, increases when the current decreases.